ESD TVS TSS DIODES IC BJT MOS LDO

Product Specification

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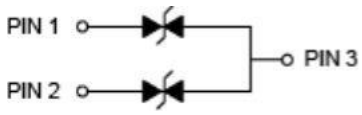
Features

◇200W(8/20μs) Peak Pulse Power
◇ High ESD Protection Level
◇ SOT323 Thin SMD Package
◇ RoHS compliant
◇ Matte Tin Lead finish (Pb-Free)◇
Protect Tw PESD2IVN-U us Lines

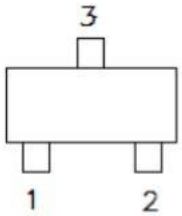
Circuit Diagram



Applications

◇ DeviceNet
◇ Low and High Speed SM24CBW
◇ Smart Distribution Systems (SDS)
◇ Controlled Area Network − ESD 1.1 / ESD FD

PIN Diagram



Ordering information

Device	Package	Reel Size	Qty / Reel
PESD2IVN-U	SOT-323	7 inch	3000

Maximum Ratings (Ta = 25℃)

Parameter		Symbol	Limit	Unit
IEC 61000-4-2 ESD Voltage	Air Model	$V_{ESD(1)}$	±25	kV
	Contact Model		±25	
JESD22-A114-B ESD Voltage	Per Human Body Model		±16	
ESD Voltage	Machine Model		±0.4	
Peak Pulse Power		$P_{PP(2)}$	200	W
Peak Pulse Current		$I_{PP(2)}$	3	A
Lead Solder Temperature − Maximum (10 Second Duration)		T_L	260	℃
Junction Temperature		T_j	150	℃
Storage Temperature Range		T_{stg}	-55 ~ +150	℃

(1).Device stressed with ten non-repetitive ESD pulses.

(2).Non-repetitive current pulse 8/20μs exponential decay waveform according to IEC61000-4-5.

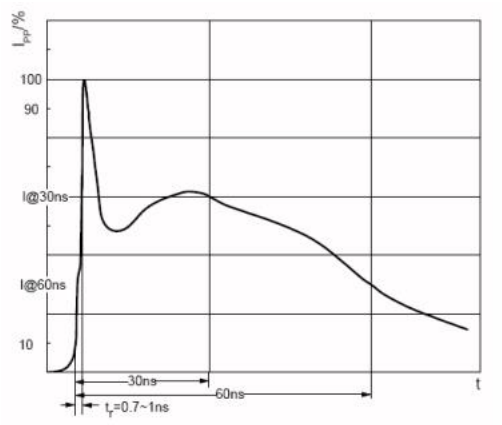
ESD standards compliance

IEC61000-4-2 Standard

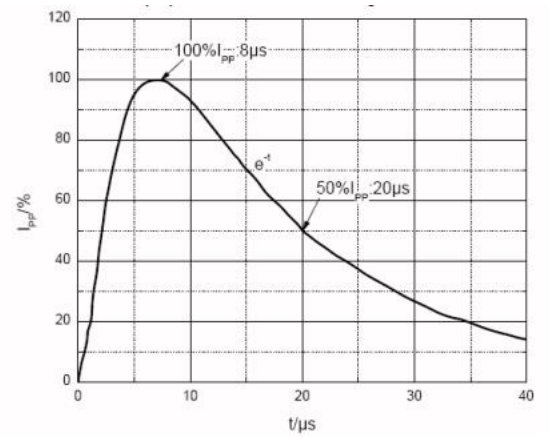
Contact Discharge		Air Discharge	
Level	Test Voltage kV	Level	Test Voltage kV
1	2	1	2
2	4	2	4
3	6	3	8
4	8	4	15

JESD22-A114-B Standard

ESD Class	Human Body Discharge V
0	0～249
1A 1B 1C	250～499 500～999 1000～1999
2	2000～3999
3A 3B	4000～7999 8000～15999

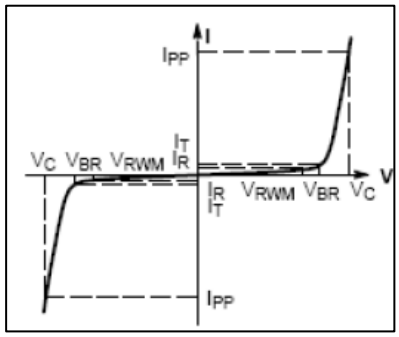


ESD pulse waveform according to IEC61000-4-2



8/20μs pulse waveform according to IEC 61000-4-5

Symbol	Parameter
V_C	Clamping Voltage @ I_{PP}
I_{PP}	Peak Pulse Current
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current
I_R	Reverse Leakage Current @ V_{RWM}
V_{RWM}	Reverse Standoff Voltage

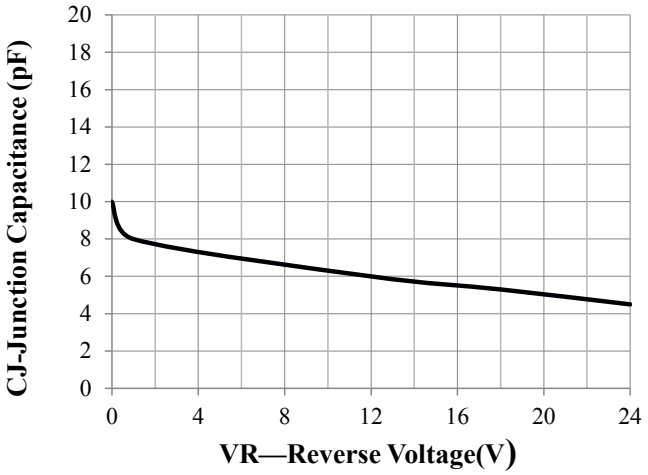


V-I characteristics for a Bi-directional TVS

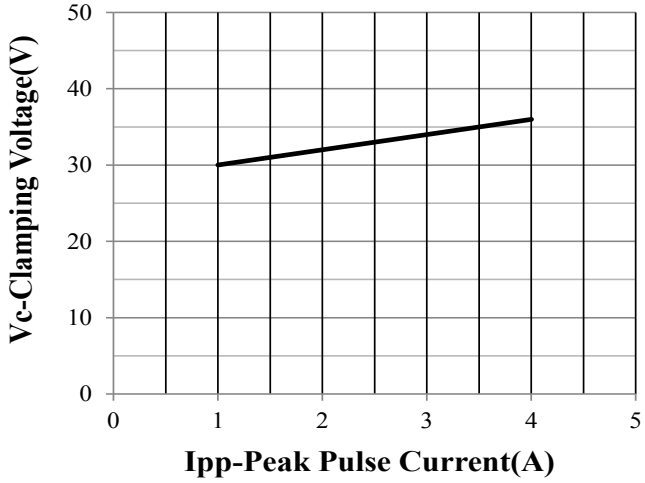
Electrical Characteristics (Ta = 25℃)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
VRWM	Reverse Working Peak Voltage				24	V
VBR	Reverse Breakdown Voltage	IT = 1mA	26.7	28	33	V
IR	Reverse Leakage Current	VRWM = 2 4 V			1	μA
VC	Clamping Voltage	IPP = 1 A (8/20μs		35	40	V
VC	Clamping Voltage	)IPP = 3 A (8/20μs)		38	60	V
Ipp	Peak Pulse Current	tp = 8/20μs			3	A
CJ	Capacitance	VR = 0V, f = 1MHz		20		pF

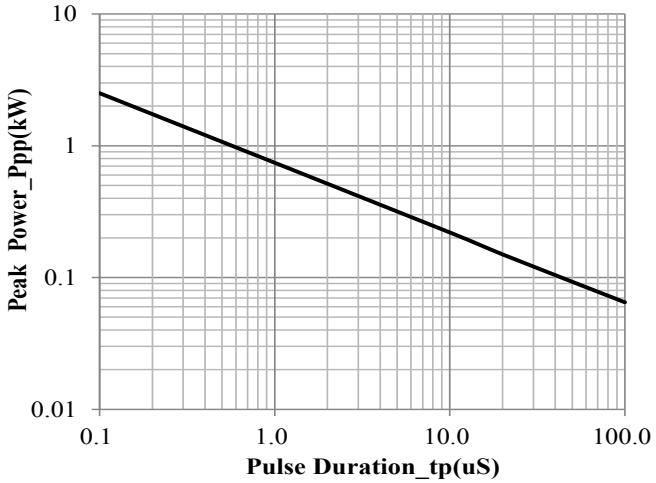
Typical Performance Characteristics (T A =25°C unless otherwise Specified)



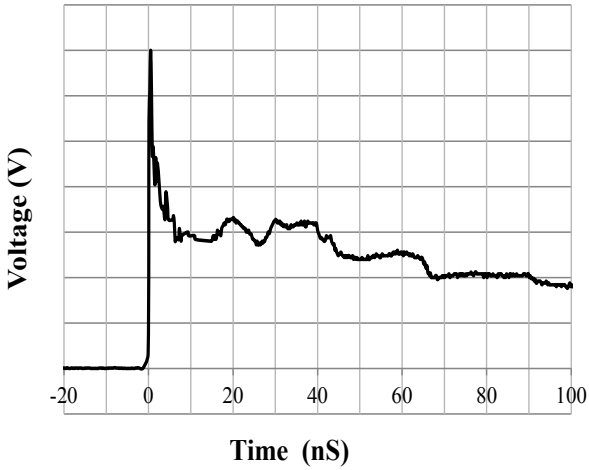
Junction Capacitance vs. Reverse Voltage



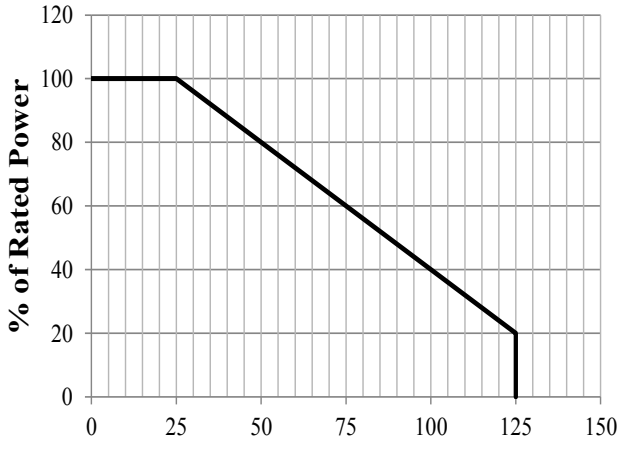
Clamping Voltage vs. Peak Pulse Current



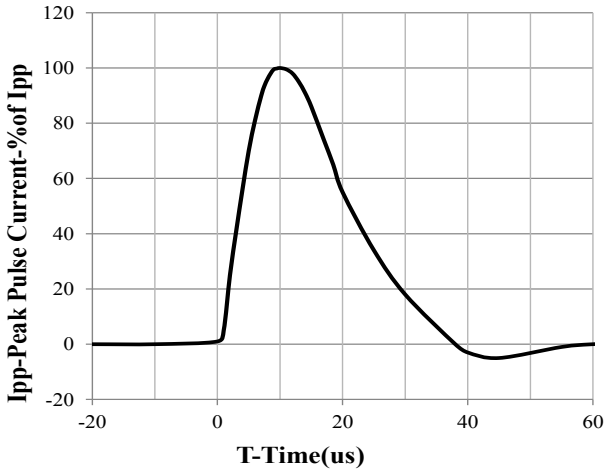
Peak Pulse Power vs. Pulse Time



IEC61000−4−2 Pulse Waveform

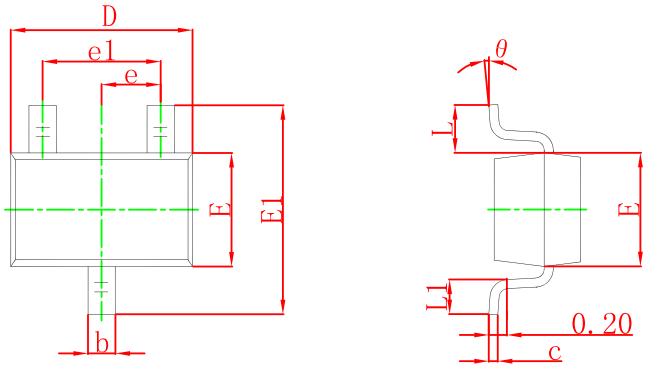


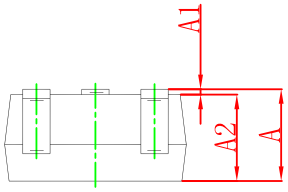
Power Derating Curve



8 X 20us Pulse Waveform

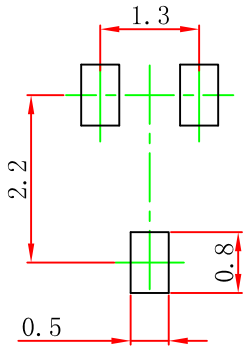
SOT-323 Package Outline Dimensions





Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

SOT-323 Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:±0.05mm.
3.The pad layout is for reference purposes only.